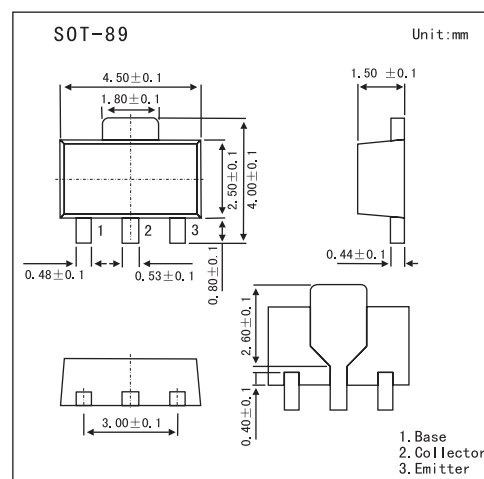


PNP Epitaxial Silicon Transistor

KSA1201

■ Features

- Collector-Emitter Voltage: $V_{CEO} = -120V$
- $f_T = 120MHz$
- Collector Power Dissipation $P_C = 1$ to $2W$: Mounted on Ceramic Board

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Base Current	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1,000	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -10mA, I_B = 0$	120			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -1mA, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -120V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE} = -5V, I_C = 0$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -5V, I_C = -100mA$	80		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$			-1.0	V
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -5V, I_C = -500mA$			-1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -5V, I_C = -100mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			30	pF

■ h_{FE} Classification

Marking	SDO	SDY
Rank	O	Y
Type	80~160	120~240